

NCE N-Channel Super Trench Power MOSFET

Description

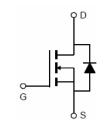
The NCEP15T11D uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

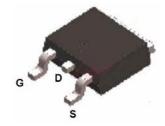
- VDS =150V,ID =110A
 RDS(ON) <7.8mΩ @ VGS=10V
- Excellent gate charge x RDS(on) product(FOM)
- Very low on-resistance RDS(on)
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic diagram



TO-263-2L top view

100% UIS TESTED!

100% AVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP15T11D	NCEP15T11D	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	150	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	110	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	93	А
Pulsed Drain Current	I _{DM}	440	А
Maximum Power Dissipation	P _D	300	W
Derating factor		2	W/℃
Single pulse avalanche energy (Note 5)	Eas	1296	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}\mathbb{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{ heta JC}$	0.5	°C/W

Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			•
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	V _{GS} =0V I _D =250μA 150		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V		-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.5	-	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =55A	-	6	7.8	mΩ
Forward Transconductance	g FS	V _{DS} =10V,I _D =55A	70	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	\/ 75\/\\ 0\/	-	10000	-	PF
Output Capacitance	Coss	$V_{DS}=75V, V_{GS}=0V,$	-	2046	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	55	-	PF
Switching Characteristics (Note 4)			•			•
Turn-on Delay Time	t _{d(on)}		-	30	-	nS
Turn-on Rise Time	t _r	V_{DD} =75 V , I_{D} =55 A	-	52	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =4.7 Ω	-	69	-	nS
Turn-Off Fall Time	t _f		-	21	-	nS
Total Gate Charge	Qg	\\ 75\\\ F6A	-	150		nC
Gate-Source Charge	Q _{gs}	V _{DS} =75V,I _D =55A,	-	50		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	26		nC
Drain-Source Diode Characteristics	1		•			
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V,I_{F}=I_{S}$	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	110	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C$, $I_F = I_S$	-	140		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	498		nC

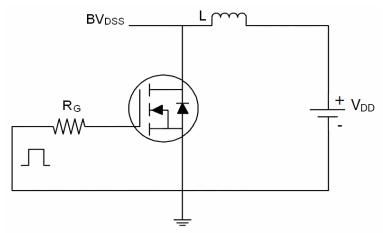
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\!\!\mathrm{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω

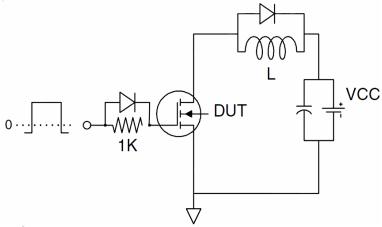


Test Circuit

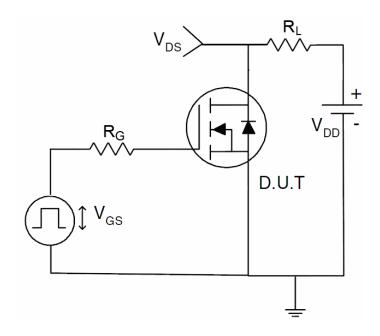
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Pb Free Product



Typical Electrical and Thermal Characteristics

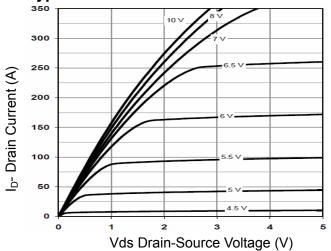


Figure 1 Output Characteristics

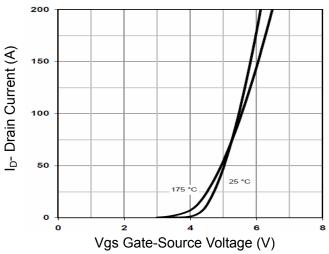


Figure 2 Transfer Characteristics

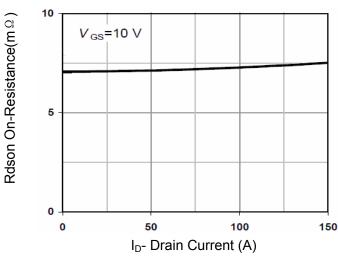


Figure 3 Rdson- Drain Current

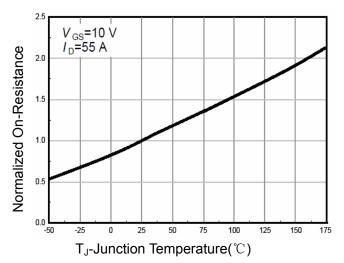


Figure 4 Rdson-JunctionTemperature

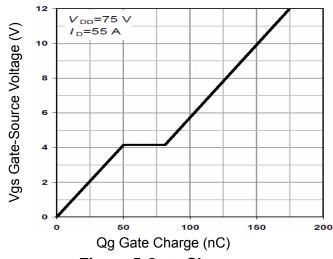


Figure 5 Gate Charge

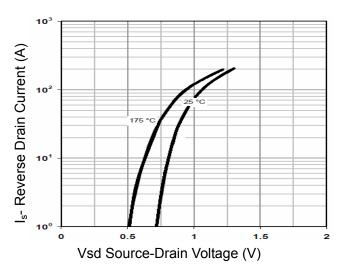
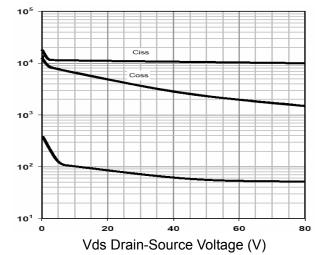


Figure 6 Source- Drain Diode Forward

Pb Free Product



C Capacitance (pF)

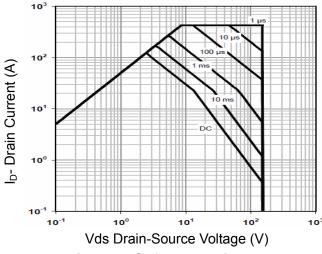


280
280
240
200
200
160
80
40
40
0
50
100
150
200

T_J-Junction Temperature(°C)

Figure 7 Capacitance vs Vds





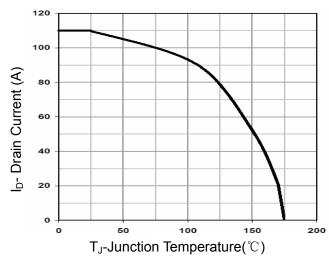


Figure 8 Safe Operation Area

Figure 10 Current De-rating

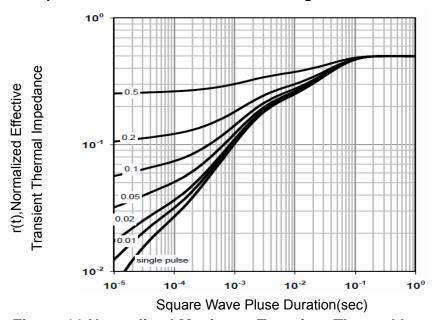
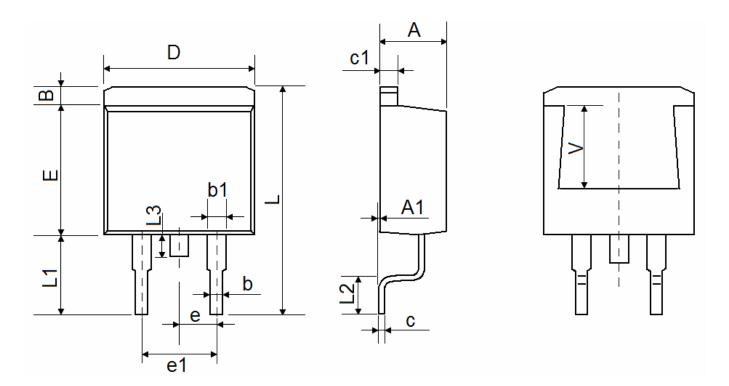


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.170	1.370	0.046	0.054	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	15.050	15.450	0.593	0.608	
L1	5.080	5.480	0.200	0.216	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
V	5.600 REF 0.220 REF			REF	



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